



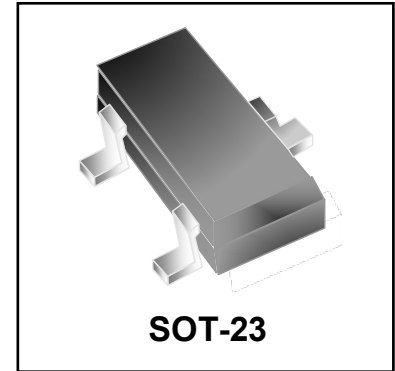
## P-Channel Enhancement MOSFET

### Features

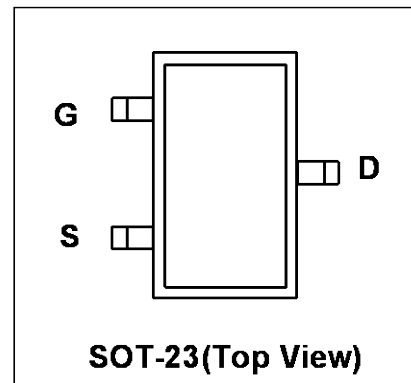
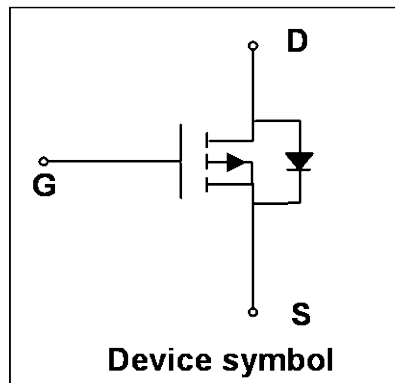
- Small Signal MOSFETs
- $V_{DS} = -30\text{ V}$ ,  $I_D = -4.2\text{ A}$   
 $R_{DS(on)} < 60\text{ m}\Omega$  @  $V_{GS} = -10\text{ V}$   
 $R_{DS(on)} < 75\text{ m}\Omega$  @  $V_{GS} = -4.5\text{ V}$
- Trench LV MOSFET Technology

### Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant



### Schematic & PIN Configuration



### Absolute Maximum Rating ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-4.2	A
$T_A = 25^\circ\text{C}$			
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	-16	A
Power Dissipation	$P_D$	1.2	W
$T_A = 25^\circ\text{C}$			
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Value	Units
Thermal Resistance from Junction to Ambient <sup>2</sup>	$R_{\theta JA}$	104	$^\circ\text{C/W}$

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	$\pm 100$	nA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.7	-1	-1.3	V
Drain-Source on-Resistance <sup>3</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.2A$	-	42	60	m $\Omega$
		$V_{GS} = -4.5V, I_D = -4A$	-	52	75	
		$V_{GS} = -2.5V, I_D = -1A$	-	60	90	
<b>Dynamic Characteristics<sup>4</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1MHz$	-	745	-	pF
Output Capacitance	$C_{oss}$		-	70	-	
Reverse Transfer Capacitance	$C_{rss}$		-	57	-	
<b>Switching Characteristics<sup>4</sup></b>						
Total Gate Charge	$Q_g$	$V_{GS} = -4.5V, V_{DS} = -15V,$ $I_D = -4.2A$	-	8	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	
Gate-Drain Charge	$Q_{gd}$		-	2.7	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -15V,$ $I_D = -4.2A, R_{GEN} = 6\Omega$	-	7	-	ns
Rise Time	$t_r$		-	3	-	
Turn-off Delay Time	$t_{d(off)}$		-	30	-	
Fall Time	$t_f$		-	12	-	
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$I_S = -4.2A, V_{GS} = 0V$	-	-	-1.2	V
Continuous Source Current	$I_S$		-	-	-4.2	A

**Notes:**

1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ\text{C}$
2. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ .
4. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

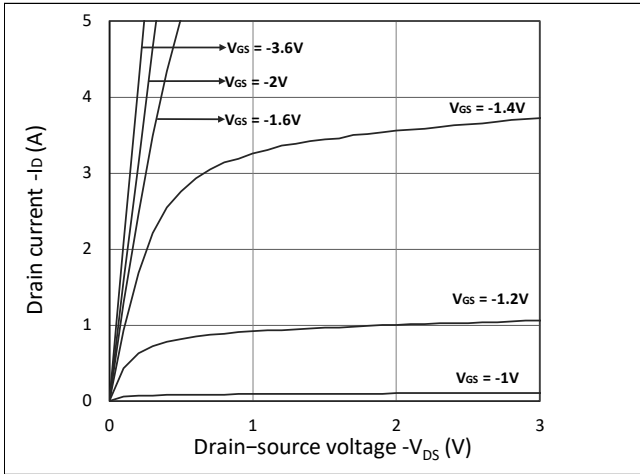


Figure 1. Output Characteristics

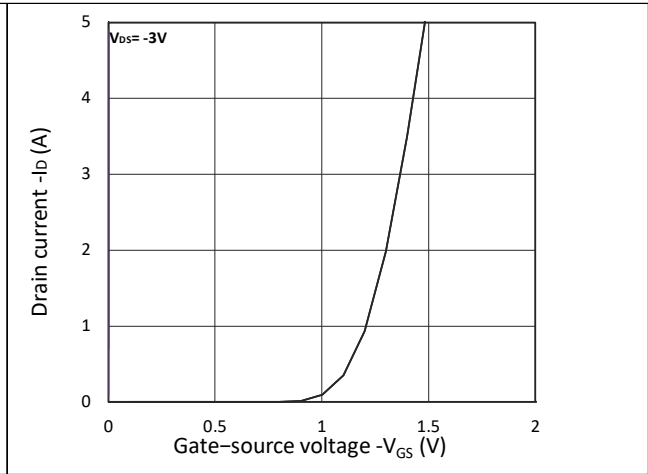


Figure 2. Transfer Characteristics

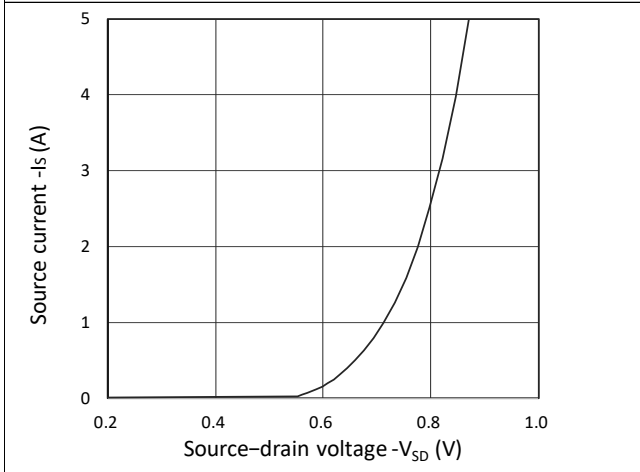


Figure 3. Forward Characteristics of Reverse

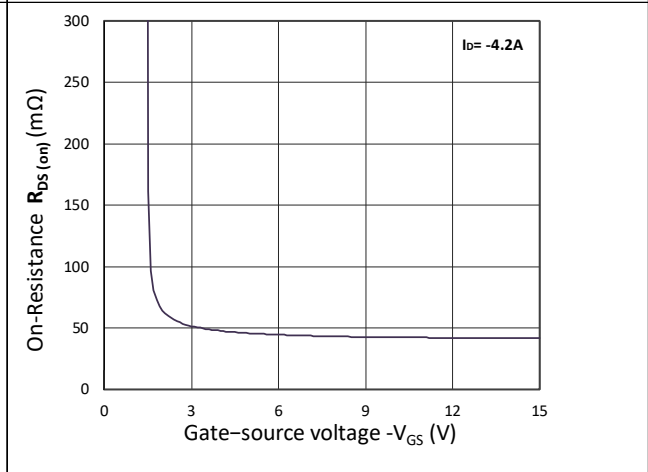


Figure 4.  $R_{DS(on)}$  vs.  $V_{GS}$

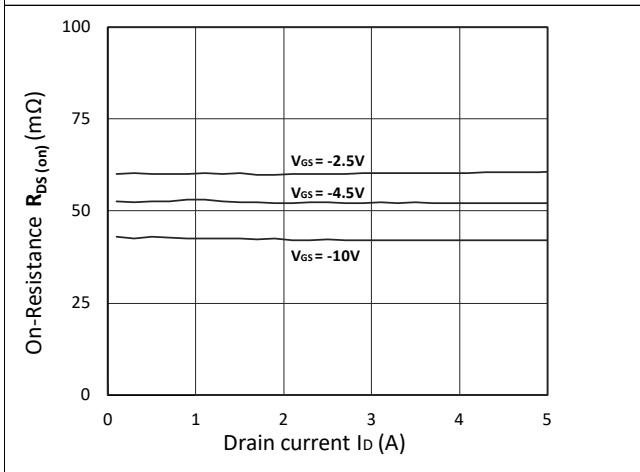


Figure 5.  $R_{DS(on)}$  vs.  $I_D$

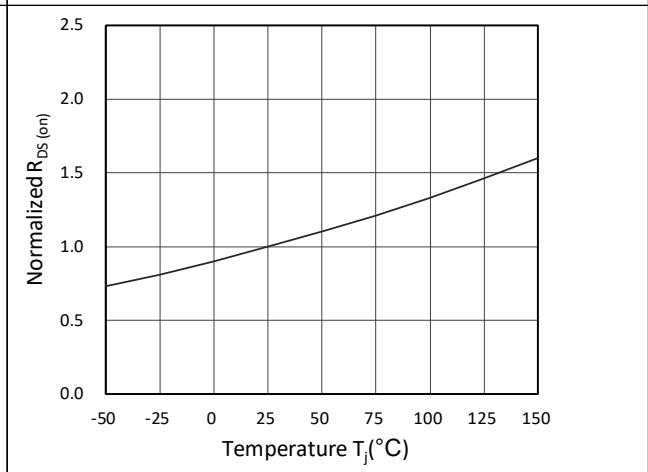


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature

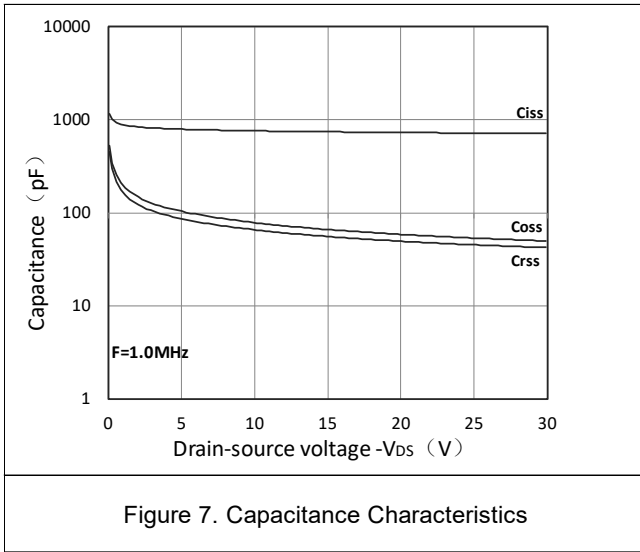


Figure 7. Capacitance Characteristics

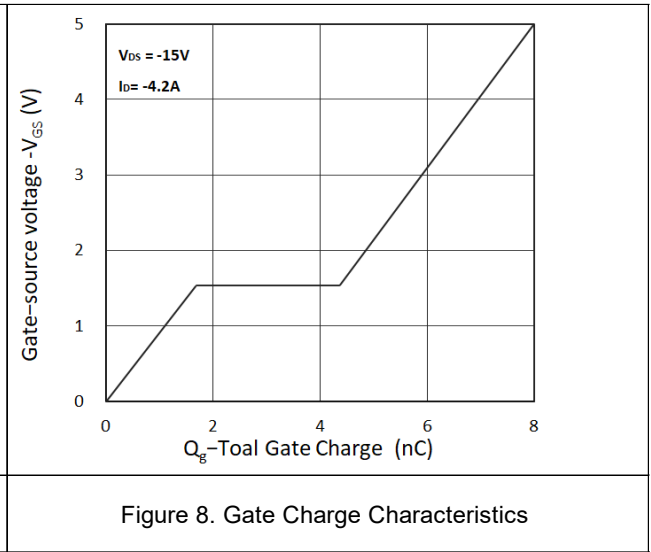


Figure 8. Gate Charge Characteristics



Outline Drawing – SOT-23

### PACKAGE OUTLINE

**SOT-23**

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

**Notes**

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

**Marking Codes**

Part Number	WD3401
Marking Code	

**Package Information**

Qty: 3k/Reel

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